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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

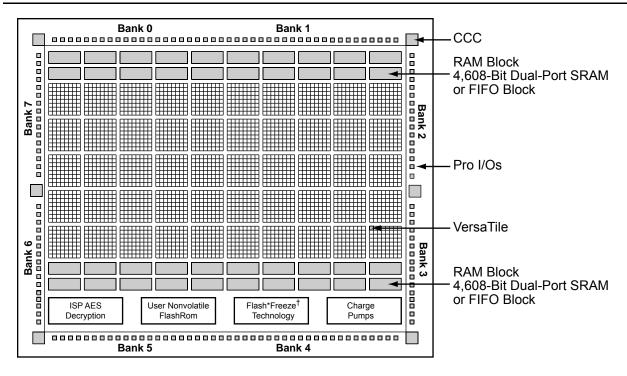
Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	·
Total RAM Bits	516096
Number of I/O	620
Number of Gates	300000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000l-1fgg896i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Microsemi

FPGA Array Architecture in Low Power Flash Devices



Note: Flash*Freeze technology only applies to IGLOOe devices.

Figure 1-7 • IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)

I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

FPGA Array Architecture in Low Power Flash Devices

Array Coordinates

During many place-and-route operations in the Microsemi Designer software tool, it is possible to set constraints that require array coordinates. Table 1-2 provides array coordinates of core cells and memory blocks for IGLOO and ProASIC3 devices. Table 1-3 provides the information for IGLOO PLUS devices. Table 1-4 on page 17 provides the information for IGLOO nano and ProASIC3 nano devices. The array coordinates are measured from the lower left (0, 0). They can be used in region constraints for specific logic groups/blocks, designated by a wildcard, and can contain core cells, memories, and I/Os.

I/O and cell coordinates are used for placement constraints. Two coordinate systems are needed because there is not a one-to-one correspondence between I/O cells and core cells. In addition, the I/O coordinate system changes depending on the die/package combination. It is not listed in Table 1-2. The Designer ChipPlanner tool provides the array coordinates of all I/O locations. I/O and cell coordinates are used for placement constraints. However, I/O placement is easier by package pin assignment.

Figure 1-9 on page 17 illustrates the array coordinates of a 600 k gate device. For more information on how to use array coordinates for region/placement constraints, see the *Designer User's Guide* or online help (available in the software) for software tools.

		VersaTiles			Memory Rows		Entire Die		
Device		Min.		Max.		Bottom	Тор	Min.	Max.
IGLOO	ProASIC3/ ProASIC3L	x	у	x	у	(x, y)	(x, y)	(x, y)	(x, y)
AGL015	A3P015	3	2	34	13	None	None	(0, 0)	(37, 15)
AGL030	A3P030	3	3	66	13	None	None	(0, 0)	(69, 15)
AGL060	A3P060	3	2	66	25	None	(3, 26)	(0, 0)	(69, 29)
AGL125	A3P125	3	2	130	25	None	(3, 26)	(0, 0)	(133, 29)
AGL250	A3P250/L	3	2	130	49	None	(3, 50)	(0, 0)	(133, 53)
AGL400	A3P400	3	2	194	49	None	(3, 50)	(0, 0)	(197, 53)
AGL600	A3P600/L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
AGL1000	A3P1000/L	3	4	258	99	(3, 2)	(3, 100)	(0, 0)	(261, 103)
AGLE600	A3PE600/L, RT3PE600L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
	A3PE1500	3	4	322	123	(3, 2)	(3, 124)	(0, 0)	(325, 127)
AGLE3000	A3PE3000/L, RT3PE3000L	3	6	450	173	(3, 2) or (3, 4)	(3, 174) or (3, 176)	(0, 0)	(453, 179)

Table 1-2 • IGLOO and ProASIC3 Array Coordinates

Table 1-3 • IGLOO PLUS Array Coordinates

		VersaTiles		Memory Rows		Entire Die		
Device	Mi	n.	Ма	ax.	Bottom	Тор	Min.	Max.
IGLOO PLUS	x	У	х	У	(x, y)	(x, y)	(x, y)	(x, y)
AGLP030	2	3	67	13	None	None	(0, 0)	(69, 15)
AGLP060	2	2	67	25	None	(3, 26)	(0, 0)	(69, 29)
AGLP125	2	2	131	25	None	(3, 26)	(0, 0)	(133, 29)

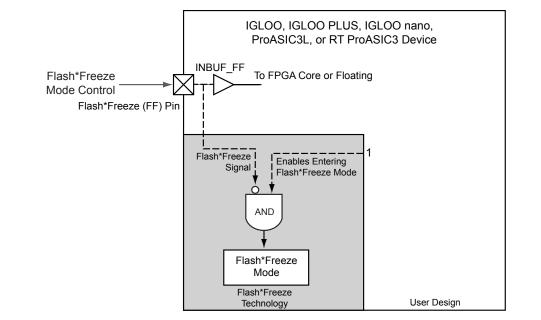


Figure 2-1 shows the concept of FF pin control in Flash*Freeze mode type 1.

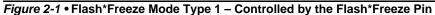


Figure 2-2 shows the timing diagram for entering and exiting Flash*Freeze mode type 1.

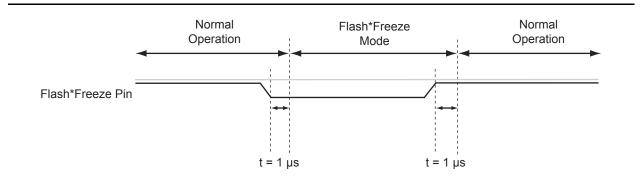


Figure 2-2 • Flash*Freeze Mode Type 1 – Timing Diagram

/О Туре	Beginning of I/O Name	Notes			
Single-Ended	GAAO/IOuxwByVz	Only one of the I/Os can be directly connected to			
	GAA1/IOuxwByVz	quadrant global at a time			
	GAA2/IOuxwByVz				
	GABO/IOuxwByVz	Only one of the I/Os can be directly connected to			
	GAB1/IOuxwByVz	quadrant global at a time.			
	GAB2/IOuxwByVz				
	GAC0/IOuxwByVz	Only one of the I/Os can be directly connected to			
	GAC1/IOuxwByVz	quadrant global at a time.			
	GAC2/IOuxwByVz				
	GBAO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GBA1/IOuxwByVz	at a time.			
	GBA2/IOuxwByVz				
	GBBO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GBB1/IOuxwByVz	at a time.			
	GBB2/IOuxwByVz				
	GBC0/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GBC1/IOuxwByVz	at a time.			
	GBC2/IOuxwByVz				
	GDAO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GDA1/IOuxwByVz	at a time.			
	GDA2/IOuxwByVz				
	GDBO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GDB1/IOuxwByVz	at a time.			
	GDB2/IOuxwByVz				
	GDC0/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GDC1/IOuxwByVz	at a time.			
	GDC2/IOuxwByVz				
	GEAO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GEA1/IOuxwByVz	at a time.			
	GEA2/IOuxwByVz				
	GEBO/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GEB1/IOuxwByVz	at a time.			
	GEB2/IOuxwByVz				
	GEC0/IOuxwByVz	Only one of the I/Os can be directly connected to a glob			
	GEC1/IOuxwByVz	at a time.			
	GEC2/IOuxwByVz				

Table 3-3 • Quadrant Global Pin Name

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

Global Buffers with PLL Function

Clocks requiring frequency synthesis or clock adjustments can utilize the PLL core before connecting to the global / quadrant global networks. A maximum of 18 CCC global buffers can be instantiated in a device—three per CCC and up to six CCCs per device. Each PLL core can generate up to three global/quadrant clocks, while a clock delay element provides one.

The PLL functionality of the clock conditioning block is supported by the PLL macro.

Clock Source	Clock Conditioning	Output
Input LVDS/LVPECL Macro	PLL Macro	GLA or GLA and (GLB or YB) or GLA and (GLC or YC) or GLA and (GLB or YB) and (GLC or YC)

Notes:

- 1. For Fusion only.
- 2. Refer to the IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide for more information.
- 3. For INBUF* driving a PLL macro or CLKDLY macro, the I/O will be hard-routed to the CCC; i.e., will be placed by software to a dedicated Global I/O.
- 4. IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Figure 4-4 • CCC Options: Global Buffers with PLL

The PLL macro provides five derived clocks (three independent) from a single reference clock. The PLL macro also provides power-down input and lock output signals. The additional inputs shown on the macro are configuration settings, which are configured through the use of SmartGen. For manual setting of these bits refer to the *IGLOO*, *ProASIC3*, *SmartFusion*, *and Fusion Macro Library Guide* for details.

Figure 4-6 on page 87 illustrates the various clock output options and delay elements.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Core Logic Clock Source

Core logic refers to internal routed nets. Internal routed signals access the CCC via the FPGA Core Fabric. Similar to the External I/O option, whenever the clock source comes internally from the core itself, the routed signal is instantiated with a PLLINT macro before connecting to the CCC clock input (see Figure 4-12 for an example illustration of the connections, shown in red).

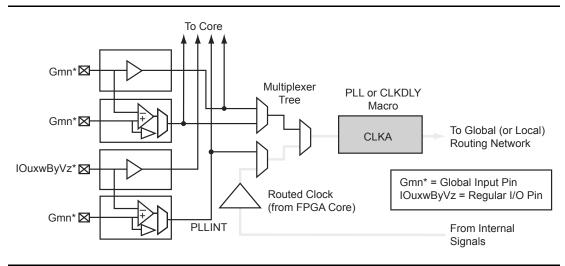


Figure 4-12 • Illustration of Core Logic Usage

For Fusion devices, the input reference clock can also be from the embedded RC oscillator and crystal oscillator. In this case, the CCC configuration is the same as the hardwired I/O clock source, and users are required to instantiate the RC oscillator or crystal oscillator macro and connect its output to the input reference clock of the CCC block.

Available I/O Standards

CLKBUF_LVCMOS5
CLKBUF_LVCMOS33 ¹
CLKBUF_LVCMOS25 ²
CLKBUF_LVCMOS18
CLKBUF_LVCMOS15
CLKBUF_PCI
CLKBUF_PCIX ³
CLKBUF_GTL25 ^{2,3}
CLKBUF_GTL33 ^{2,3}
CLKBUF_GTLP25 ^{2,3}
CLKBUF_GTLP33 ^{2,3}
CLKBUF_HSTL_I ^{2,3}
CLKBUF_HSTL_II ^{2,3}
CLKBUF_SSTL3_I ^{2,3}
CLKBUF_SSTL3_II ^{2,3}
CLKBUF_SSTL2_I ^{2,3}
CLKBUF_SSTL2_II ^{2,3}
CLKBUF_LVDS ^{4,5}
CLKBUF_LVPECL ⁵

Notes:

- 1. By default, the CLKBUF macro uses 3.3 V LVTTL I/O technology. For more details, refer to the IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide.
- 2. I/O standards only supported in ProASIC3E and IGLOOe families.
- 3. I/O standards only supported in the following Fusion devices: AFS600 and AFS1500.
- 4. B-LVDS and M-LVDS standards are supported by CLKBUF_LVDS.
- 5. Not supported for IGLOO nano and ProASIC3 nano devices.

Global Synthesis Constraints

The Synplify[®] synthesis tool, by default, allows six clocks in a design for Fusion, IGLOO, and ProASIC3. When more than six clocks are needed in the design, a user synthesis constraint attribute, syn_global_buffers, can be used to control the maximum number of clocks (up to 18) that can be inferred by the synthesis engine.

High-fanout nets will be inferred with clock buffers and/or internal clock buffers. If the design consists of CCC global buffers, they are included in the count of clocks in the design.

The subsections below discuss the clock input source (global buffers with no programmable delays) and the clock conditioning functional block (global buffers with programmable delays and/or PLL function) in detail.

Figure 4-36 • Second-Stage PLL Showing Input of 256 MHz from First Stage and Final Output of 280 MHz

Figure 4-37 shows the simulation results, where the first PLL's output period is 3.9 ns (~256 MHz), and the stage 2 (final) output period is 3.56 ns (~280 MHz).

Stage 2 Output Clock Period Stage 1 Output Clock Period

Figure 4-37 • Model Sim Simulation Results

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Recommended Board-Level Considerations

The power to the PLL core is supplied by VCCPLA/B/C/D/E/F (VCCPLx), and the associated ground connections are supplied by VCOMPLA/B/C/D/E/F (VCOMPLx). When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Optionally, the PLL can be turned on/off during normal device operation via the POWERDOWN port (see Table 4-3 on page 84).

PLL Power Supply Decoupling Scheme

The PLL core is designed to tolerate noise levels on the PLL power supply as specified in the datasheets. When operated within the noise limits, the PLL will meet the output peak-to-peak jitter specifications specified in the datasheets. User applications should always ensure the PLL power supply is powered from a noise-free or low-noise power source.

However, in situations where the PLL power supply noise level is higher than the tolerable limits, various decoupling schemes can be designed to suppress noise to the PLL power supply. An example is provided in Figure 4-38. The VCCPLx and VCOMPLx pins correspond to the PLL analog power supply and ground.

Microsemi strongly recommends that two ceramic capacitors (10 nF in parallel with 100 nF) be placed close to the power pins (less than 1 inch away). A third generic 10 μ F electrolytic capacitor is recommended for low-frequency noise and should be placed farther away due to its large physical size. Microsemi recommends that a 6.8 μ H inductor be placed between the supply source and the capacitors to filter out any low-/medium- and high-frequency noise. In addition, the PCB layers should be controlled so the VCCPLx and VCOMPLx planes have the minimum separation possible, thus generating a good-quality RF capacitor.

For more recommendations, refer to the Board-Level Considerations application note.

Recommended 100 nF capacitor:

- Producer BC Components, type X7R, 100 nF, 16 V
- BC Components part number: 0603B104K160BT
- Digi-Key part number: BC1254CT-ND
- Digi-Key part number: BC1254TR-ND

Recommended 10 nF capacitor:

- Surface-mount ceramic capacitor
- Producer BC Components, type X7R, 10 nF, 50 V
- BC Components part number: 0603B103K500BT
- Digi-Key part number: BC1252CT-ND
- Digi-Key part number: BC1252TR-ND

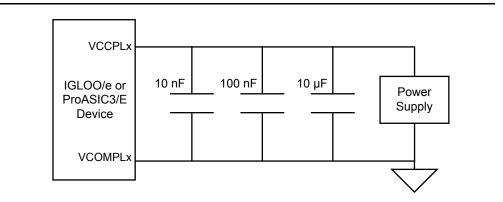


Figure 4-38 • Decoupling Scheme for One PLL (should be replicated for each PLL used)

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, ADDRB should be tied to ground.

	ADDRx		
D×W	Unused	Used	
4k×1	None	[11:0]	
2k×2	[11]	[10:0]	
1k×4	[11:10]	[9:0]	
512×9	[11:9]	[8:0]	

Note: The "x" in ADDRx implies A or B.

DINA and DINB

These are the input data signals, and they are nine bits wide. Not all nine bits are valid in all configurations. When a data width less than nine is specified, unused high-order signals must be grounded (Table 6-4).

Note: When using the SRAM in single-port mode for Automotive ProASIC3 devices, DINB should be tied to ground.

DOUTA and DOUTB

These are the nine-bit output data signals. Not all nine bits are valid in all configurations. As with DINA and DINB, high-order bits may not be used (Table 6-4). The output data on unused pins is undefined.

	DINx/DOUTx		
D×W	Unused	Used	
4k×1	[8:1]	[0]	
2k×2	[8:2]	[1:0]	
1k×4	[8:4]	[3:0]	
512×9	None	[8:0]	

Note: The "x" in DINx or DOUTx implies A or B.

RAM512X18 Macro

RAM512X18 is the two-port configuration of the same RAM block (Figure 6-5 on page 156). Like the RAM4K9 nomenclature, the RAM512X18 nomenclature refers to both the deepest possible configuration and the widest possible configuration the two-port RAM block can assume. In two-port mode, the RAM block can be configured to either the 512×9 aspect ratio or the 256×18 aspect ratio. RAM512X18 is also fully synchronous and has the following features:

- Dedicated read and write ports
- · Active-low read and write enables
- · Selectable pipelined or nonpipelined read
- Active-low asynchronous reset
- Designer software will automatically facilitate falling-edge clocks by bubble-pushing the inversion to previous stages.



I/O Structures in IGLOO and ProASIC3 Devices

5 V Input and Output Tolerance

IGLOO and ProASIC3 devices are both 5 V-input– and 5 V–output–tolerant if certain I/O standards are selected. Table 7-5 on page 179 shows the I/O standards that support 5 V input tolerance. Only 3.3 V LVTTL/LVCMOS standards support 5 V output tolerance. Refer to the appropriate family datasheet for the detailed description and configuration information.

This feature is not shown in the I/O Attribute Editor.

5 V Input Tolerance

I/Os can support 5 V input tolerance when LVTTL 3.3 V, LVCMOS 3.3 V, LVCMOS 2.5 V, and LVCMOS 2.5 V / 5.0 V configurations are used (see Table 7-12 on page 193). There are four recommended solutions for achieving 5 V receiver tolerance (see Figure 7-9 on page 195 to Figure 7-12 on page 197 for details of board and macro setups). All the solutions meet a common requirement of limiting the voltage at the input to 3.6 V or less. In fact, the I/O absolute maximum voltage rating is 3.6 V, and any voltage above 3.6 V may cause long-term gate oxide failures.

Solution 1

The board-level design must ensure that the reflected waveform at the pad does not exceed the limits provided in the recommended operating conditions in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the two external resistors as explained below. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

This solution requires two board resistors, as demonstrated in Figure 7-9 on page 195. Here are some examples of possible resistor values (based on a simplified simulation model with no line effects and 10 Ω transmitter output resistance, where Rtx_out_high = (VCCI – VOH) / I_{OH} and Rtx_out_low = VOL / I_{OL}).

Example 1 (high speed, high current):

Rtx_out_high = Rtx_out_low = 10
$$\Omega$$

R1 = 36 Ω (±5%), P(r1)min = 0.069 Ω

R2 = 82 Ω (±5%), P(r2)min = 0.158 Ω

Imax_tx = 5.5 V / (82 × 0.95 + 36 × 0.95 + 10) = 45.04 mA

t_{RISE} = t_{FALL} = 0.85 ns at C_pad_load = 10 pF (includes up to 25% safety margin)

t_{RISE} = t_{FALL} = 4 ns at C_pad_load = 50 pF (includes up to 25% safety margin)

Example 2 (low-medium speed, medium current):

 $Rtx_out_high = Rtx_out_low = 10 \Omega$

R1 = 220 Ω (±5%), P(r1)min = 0.018 Ω

R2 = 390 Ω (±5%), P(r2)min = 0.032 Ω

Imax_tx = 5.5 V / (220 × 0.95 + 390 × 0.95 + 10) = 9.17 mA

t_{RISE} = t_{FALL} = 4 ns at C_pad_load = 10 pF (includes up to 25% safety margin)

t_{RISE} = t_{FALL} = 20 ns at C_pad_load = 50 pF (includes up to 25% safety margin)

Other values of resistors are also allowed as long as the resistors are sized appropriately to limit the voltage at the receiving end to 2.5 V < Vin (rx) < 3.6 V when the transmitter sends a logic 1. This range of Vin_dc(rx) must be assured for any combination of transmitter supply (5 V ± 0.5 V), transmitter output resistance, and board resistor tolerances.

8 – I/O Structures in IGLOOe and ProASIC3E Devices

Introduction

Low power flash devices feature a flexible I/O structure, supporting a range of mixed voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V) through bank-selectable voltages. IGLOO[®]e, ProASIC[®]3EL, and ProASIC3E families support Pro I/Os.

Users designing I/O solutions are faced with a number of implementation decisions and configuration choices that can directly impact the efficiency and effectiveness of their final design. The flexible I/O structure, supporting a wide variety of voltages and I/O standards, enables users to meet the growing challenges of their many diverse applications. The Libero SoC software provides an easy way to implement I/O that will result in robust I/O design.

This document first describes the two different I/O types in terms of the standards and features they support. It then explains the individual features and how to implement them in Libero SoC.

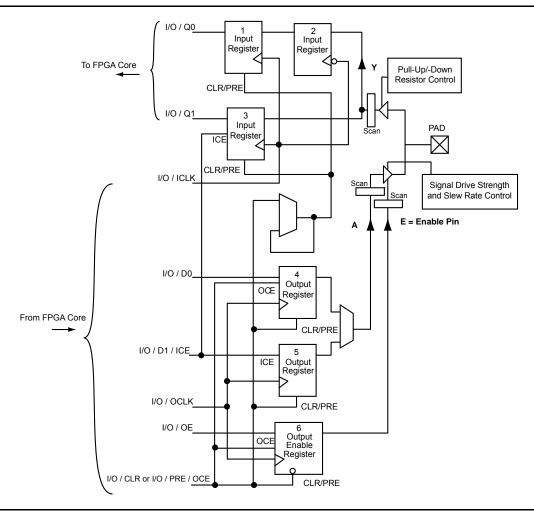


Figure 8-1 • DDR Configured I/O Block Logical Representation

I/O Register Combining

Every I/O has several embedded registers in the I/O tile that are close to the I/O pads. Rather than using the internal register from the core, the user has the option of using these registers for faster clock-to-out timing, and external hold and setup. When combining these registers at the I/O buffer, some architectural rules must be met. Provided these rules are met, the user can enable register combining globally during Compile (as shown in the "Compiling the Design" section on page 261).

This feature is supported by all I/O standards.

Rules for Registered I/O Function

- 1. The fanout between an I/O pin (D, Y, or E) and a register must be equal to one for combining to be considered on that pin.
- 2. All registers (Input, Output, and Output Enable) connected to an I/O must share the same clear or preset function:
 - If one of the registers has a CLR pin, all the other registers that are candidates for combining in the I/O must have a CLR pin.
 - If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
 - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
 - If the clear or preset pins are present, they must have the same polarity.
 - If the clear or preset pins are present, they must be driven by the same signal (net).
- 3. Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
 - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
 - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a bibuf while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

When the I/O is pulled up, it is connected to the VCCI of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to the "Flash*Freeze Technology and Low Power Modes in IGLOO and ProASIC3L Devices" chapter in the *IGLOOe FPGA Fabric User's Guide* or *ProASIC3E FPGA Fabric User's Guide* for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions. Slew rate control is available for LVTTL, LVCMOS, and PCI-X I/O standards. The other I/O standards have a preset slew value.

The slew rate can be implemented by using a PDC command (Table 8-6 on page 218), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

If the assignment is not successful, an error message appears in the Output window.

To undo the I/O bank assignments, choose **Undo** from the **Edit** menu. Undo removes the I/O technologies assigned by the IOBA. It does not remove the I/O technologies previously assigned.

To redo the changes undone by the Undo command, choose Redo from the Edit menu.

To clear I/O bank assignments made before using the Undo command, manually unassign or reassign I/O technologies to banks. To do so, choose **I/O Bank Settings** from the **Edit** menu to display the I/O Bank Settings dialog box.

Conclusion

Fusion, IGLOO, and ProASIC3 support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

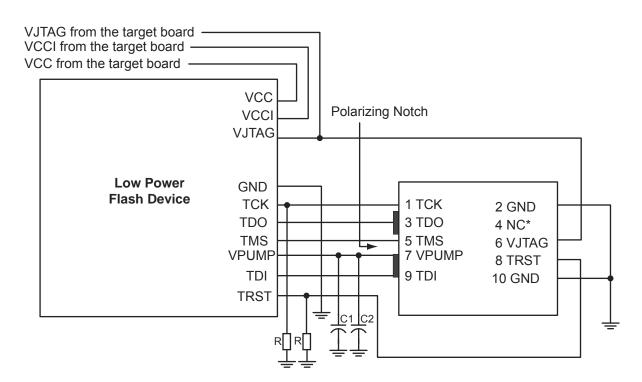
Related Documents

User's Guides

Libero SoC User's Guide http://www.microsemi.com/soc/documents/libero_ug.pdf IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf SmartGen Core Reference Guide http://www.microsemi.com/soc/documents/genguide ug.pdf

Board-Level Considerations

A bypass capacitor is required from VPUMP to GND for all low power flash devices during programming. This bypass capacitor protects the devices from voltage spikes that may occur on the VPUMP supplies during the erase and programming cycles. Refer to the "Pin Descriptions and Packaging" chapter of the appropriate device datasheet for specific recommendations. For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible. The bypass capacitor must be placed within 2.5 cm of the device pins.



Note: *NC (FlashPro3/3X); Prog_Mode (FlashPro4). Prog_Mode on FlashPro4 is an output signal that goes High during device programming and returns to Low when programming is complete. This signal can be used to drive a system to provide a 1.5 V programming signal to IGLOO nano, ProASIC3L, and RT ProASIC3 devices that can run with 1.2 V core voltage but require 1.5 V for programming. IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only), but IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.

Figure 13-6 • Board Layout and Programming Header Top View

Troubleshooting Signal Integrity

Symptoms of a Signal Integrity Problem

A signal integrity problem can manifest itself in many ways. The problem may show up as extra or dropped bits during serial communication, changing the meaning of the communication. There is a normal variation of threshold voltage and frequency response between parts even from the same lot. Because of this, the effects of signal integrity may not always affect different devices on the same board in the same way. Sometimes, replacing a device appears to make signal integrity problems go away, but this is just masking the problem. Different parts on identical boards will exhibit the same problem sooner or later. It is important to fix signal integrity problems early. Unless the signal integrity problems are severe enough to completely block all communication between the device and the programmer, they may show up as subtle problems. Some of the FlashPro4/3/3X exit codes that are caused by signal integrity problems are not the only possible cause of these

Microsemi

Microprocessor Programming of Microsemi's Low Power Flash Devices

Microprocessor Programming Support in Flash Devices

The flash-based FPGAs listed in Table 15-1 support programming with a microprocessor and the functions described in this document.

Table 15-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

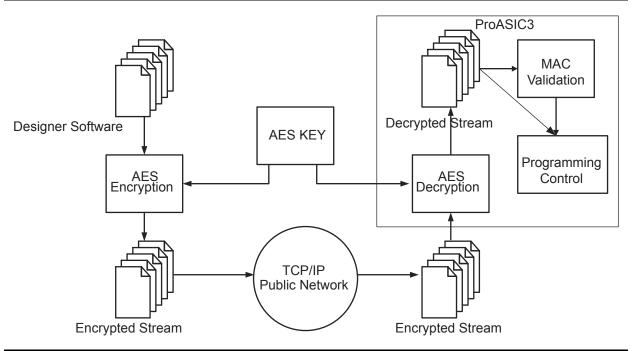
IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 15-1. Where the information applies to only one device or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 15-1. Where the information applies to only one device or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



useless to the thief. To learn more about the low power flash devices' security features, refer to the "Security in Low Power Flash Devices" section on page 301.

Figure 15-5 • ProASIC3 Device Encryption Flow

Conclusion

The Fusion, IGLOO, and ProASIC3 FPGAs are ideal for applications that require field upgrades. The single-chip devices save board space by eliminating the need for EEPROM. The built-in AES with MAC enables transmission of programming data over any network without fear of design theft. Fusion, IGLOO, and ProASIC3 FPGAs are IEEE 1532–compliant and support STAPL, making the target programming software easy to implement.

17 – UJTAG Applications in Microsemi's Low Power Flash Devices

Introduction

In Fusion, IGLOO, and ProASIC3 devices, there is bidirectional access from the JTAG port to the core VersaTiles during normal operation of the device (Figure 17-1). User JTAG (UJTAG) is the ability for the design to use the JTAG ports for access to the device for updates, etc. While regular JTAG is used, the UJTAG tiles, located at the southeast area of the die, are directly connected to the JTAG Test Access Port (TAP) Controller in normal operating mode. As a result, all the functional blocks of the device, such as Clock Conditioning Circuits (CCCs) with PLLs, SRAM blocks, embedded FlashROM, flash memory blocks, and I/O tiles, can be reached via the JTAG ports. The UJTAG functionality is available by instantiating the UJTAG macro directly in the source code of a design. Access to the FPGA core VersaTiles from the JTAG ports enables users to implement different applications using the TAP Controller (JTAG port). This document introduces the UJTAG tile functionality and discusses a few application examples. However, the possible applications are not limited to what is presented in this document. UJTAG can serve different purposes in many designs as an elementary or auxiliary part of the design. For detailed usage information, refer to the "Boundary Scan in Low Power Flash Devices" section on page 357.

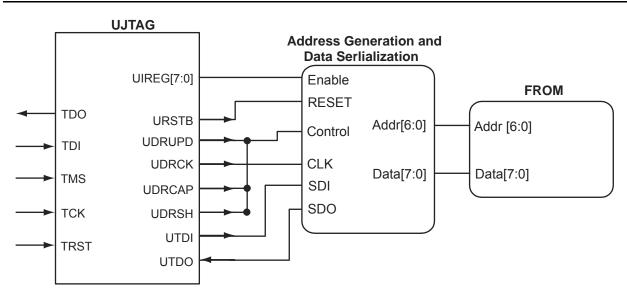


Figure 17-1 • Block Diagram of Using UJTAG to Read FlashROM Contents

Fine Tuning

In some applications, design constants or parameters need to be modified after programming the original design. The tuning process can be done using the UJTAG tile without reprogramming the device with new values. If the parameters or constants of a design are stored in distributed registers or embedded SRAM blocks, the new values can be shifted onto the JTAG TAP Controller pins, replacing the old values. The UJTAG tile is used as the "bridge" for data transfer between the JTAG pins and the FPGA VersaTiles or SRAM logic. Figure 17-5 shows a flow chart example for fine-tuning application steps using the UJTAG tile.

In Figure 17-5, the TMS signal sets the TAP Controller state machine to the appropriate states. The flow mainly consists of two steps: a) shifting the defined instruction and b) shifting the new data. If the target parameter is constantly used in the design, the new data can be shifted into a temporary shift register from UTDI. The UDRSH output of UJTAG can be used as a shift-enable signal, and UDRCK is the shift clock to the shift register. Once the shift process is completed and the TAP Controller state is moved to the Update_DR state, the UDRUPD output of the UJTAG can latch the new parameter value from the temporary register into a permanent location. This avoids any interruption or malfunctioning during the serial shift of the new value.

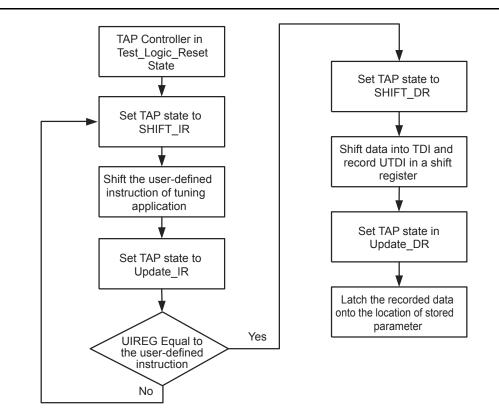


Figure 17-5 • Flow Chart Example of Fine-Tuning an Application Using UJTAG